

SANYO	No.1881A	DRA03T Silicon Planar Type 0.3A Reverse Blocking Thyristor
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Features

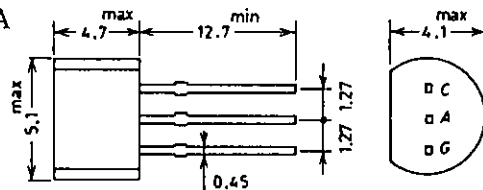
- Low-power switching and control
- Small size and light weight
- Peak OFF-state (reverse) voltage : - 100 to - 600V
- Average ON-state current : 0.3A
- TO92 package

Absolute Maximum Ratings at Ta = 25°C			DRA03TB	DRA03TC	DRA03TE	DRA03TG	unit
Repetitive Peak OFF-State Voltage	V _{DRM}	R _{GK} = 1Ω	100	200	400	600	V
Non-Repetitive Peak Reverse Voltage	V _{RSM}	R _{GK} = 1Ω	- 150	- 300	- 500	- 720	V
Repetitive Peak Reverse Voltage	V _{RRM}	R _{GK} = 1Ω	- 100	- 200	- 400	- 600	V
Average ON-State Current	I _{T(AV)}	Ta = 30°C, single-phase half-wave	→	→	→	0.3	A
RMS ON-State Current	I _{T(RMS)}		→	→	→	0.45	A
Surge ON-State Current	I _{TSM}	Sine half-wave 1 cycle, 50Hz	→	→	→	9	A
Amperes Squared-Seconds	∫i ² T·dt	1ms ≤ t ≤ 10ms	→	→	→	0.4	A ² S
Peak Gate Power Dissipation	P _{GM}	f ≥ 50Hz, duty ≤ 10%	→	→	→	0.1	W
Average Gate Power Dissipation	P _{G(AV)}		→	→	→	0.01	W
Peak Gate Forward Current	I _{FGM}	f ≥ 50Hz, duty ≤ 10%	→	→	→	0.125	A
Peak Gate Forward Voltage	V _{FGM}	f ≥ 50Hz, duty ≤ 10%	→	→	→	3.5	V
Peak Gate Reverse Voltage	V _{RCM}		→	→	→	- 5	V
Junction Temperature	T _J		→	→	→	110	°C
Storage Temperature	T _{stg}		→	→	→	- 40 to + 125	°C
Weight			→	→	→	0.2	g

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Repetitive Peak OFF-State Current	I _{DRM}	T _J = 110°C, V _D = V _{DRM} , R _{GK} = 1kΩ			0.1	mA
Repetitive Peak Reverse Current	I _{RRM}	T _J = 110°C, V _D = V _{RRM} , R _{GK} = 1kΩ			0.1	mA
ON-State Voltage	V _T	I _T = 2A			2.0	V
Holding Current	I _H	R _L = 100Ω, R _{GK} = 1kΩ		4.0		mA
Gate Trigger Current	I _{GT}	V _D = 6V, R _L = 100Ω, R _{GK} = 1kΩ			0.2	mA
Gate Trigger Voltage	V _{GT}	V _D = 6V, R _L = 100Ω, R _{GK} = 1kΩ			0.8	V
Gate Nontrigger Voltage	V _{GD}	Ta = 110°C, V _D = 6V, R _{GK} = 1kΩ	0.2			V
Thermal Resistance	R _{th(j-c)}				250	°C/W

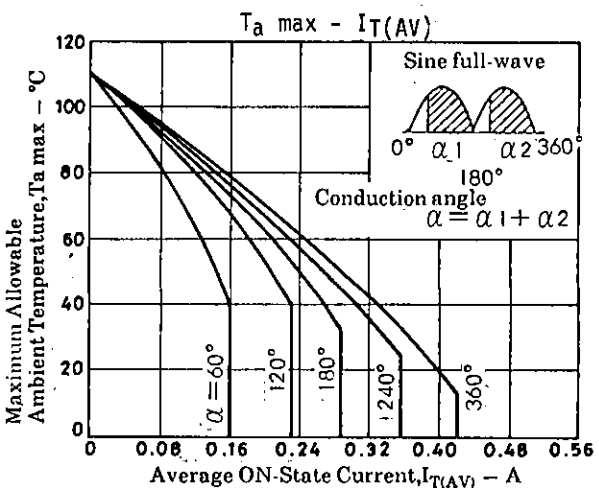
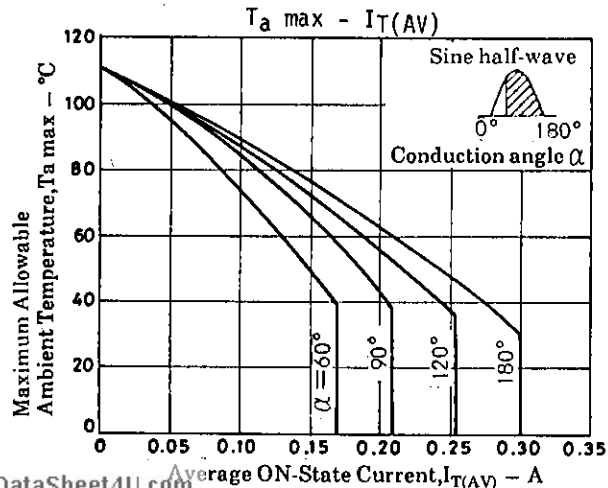
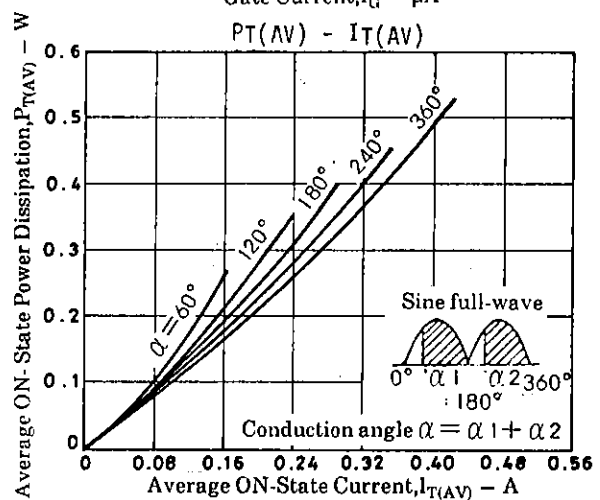
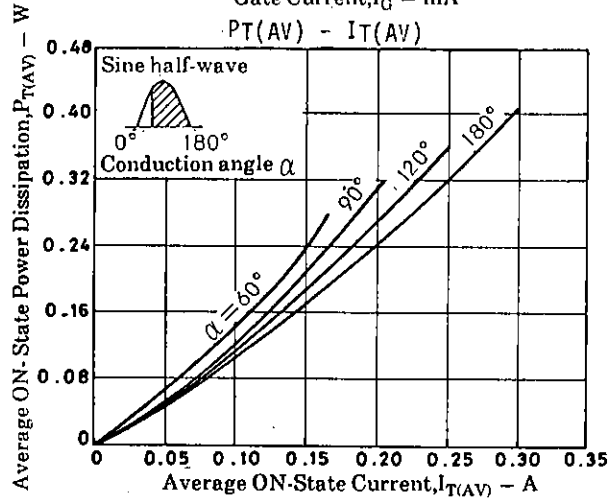
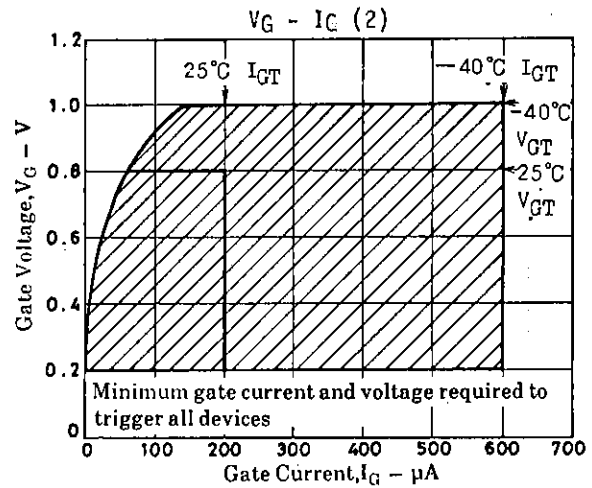
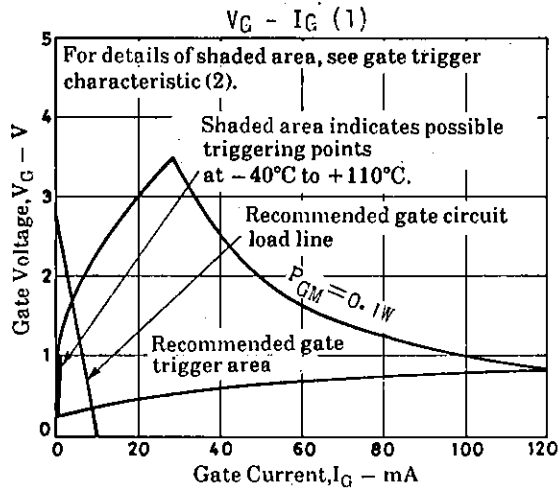
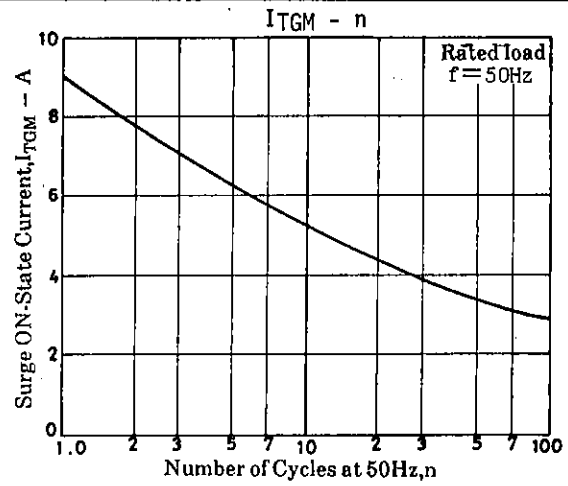
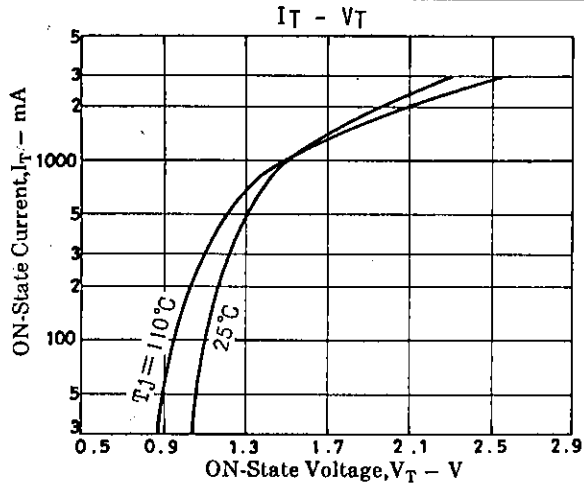
Package Dimensions 1096A
(unit: mm)

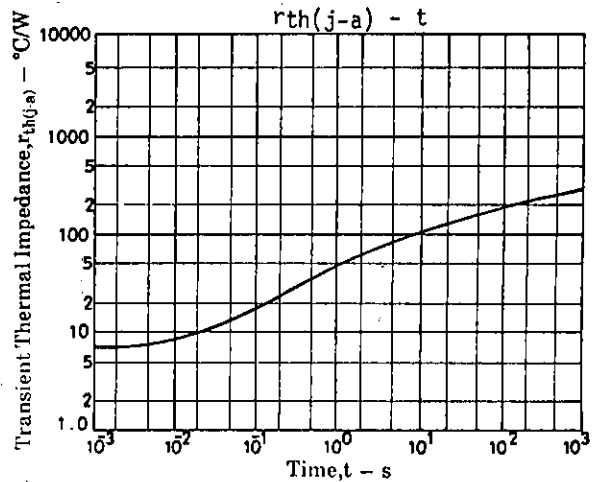
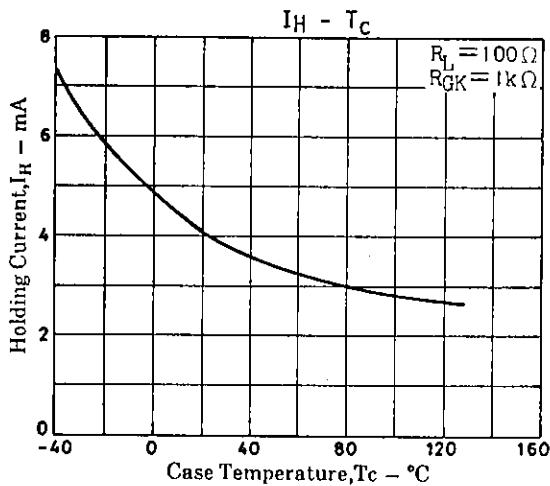
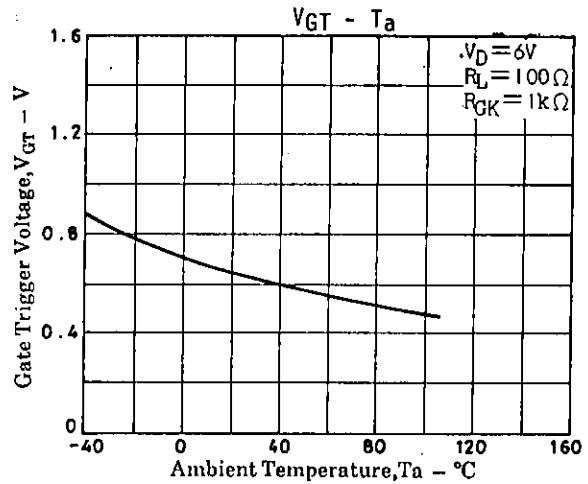
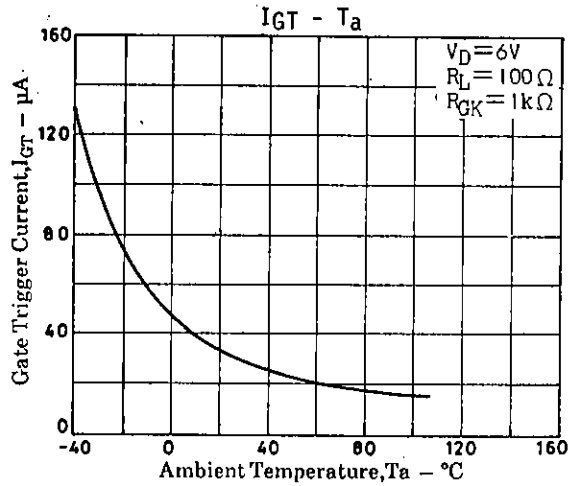


C: Cathode
A: Anode
G: Gate

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